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[IXKP10N60C5](#)

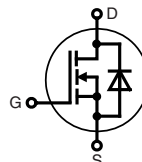
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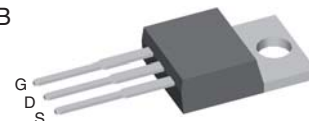
CoolMOS™ 1, Power MOSFET

N-Channel Enhancement Mode
 Low $R_{DS(on)}$, High V_{DSS} MOSFET
 Ultra low gate charge

$I_{D25} = 10\text{ A}$
 $V_{DSS} = 600\text{ V}$
 $R_{DS(on)\text{ max}} = 0.385\ \Omega$



TO-220 AB



MOSFET			
Symbol	Conditions	Maximum Ratings	
V_{DSS}	$T_{VJ} = 25^\circ\text{C}$	600	V
V_{GS}		± 20	V
I_{D25}	$T_C = 25^\circ\text{C}$	10	A
I_{D90}	$T_C = 90^\circ\text{C}$	7	A
E_{AS}	single pulse } $I_D = 3.4\text{ A}; T_C = 25^\circ\text{C}$ repetitive	225	mJ
E_{AR}		0.3	mJ
dV/dt	MOSFET dV/dt ruggedness $V_{DS} = 0 \dots 480\text{ V}$	50	V/ns

Features

- fast CoolMOS™ 1) power MOSFET 4th generation
- High blocking capability
- Lowest resistance
- Avalanche rated for unclamped inductive switching (UIS)
- Low thermal resistance due to reduced chip thickness
- Enhanced total power density

Applications

- Switched mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Power factor correction (PFC)
- Welding
- Inductive heating
- PDP and LCD adapter

1) CoolMOS™ is a trademark of Infineon Technologies AG.

Symbol	Conditions	Characteristic Values			
		(T _{VJ} = 25°C, unless otherwise specified)			
		min.	typ.	max.	
$R_{DS(on)}$	$V_{GS} = 10\text{ V}; I_D = 5.2\text{ A}$		350	385	mΩ
$V_{GS(th)}$	$V_{DS} = V_{GS}; I_D = 0.34\text{ mA}$	2.5	3	3.5	V
I_{DSS}	$V_{DS} = 600\text{ V}; V_{GS} = 0\text{ V}$			1	μA
				10	μA
I_{GSS}	$V_{GS} = \pm 20\text{ V}; V_{DS} = 0\text{ V}$			100	nA
C_{iss}	} $V_{GS} = 0\text{ V}; V_{DS} = 100\text{ V}$ $f = 1\text{ MHz}$		790		pF
C_{oss}				38	
Q_g	} $V_{GS} = 0\text{ to }10\text{ V}; V_{DS} = 400\text{ V}; I_D = 5.2\text{ A}$		17	22	ns
Q_{gs}			4		ns
Q_{gd}			6		ns
$t_{d(on)}$	} $V_{GS} = 10\text{ V}; V_{DS} = 400\text{ V}$ $I_D = 5.2\text{ A}; R_G = 3.3\ \Omega$		10		ns
t_r			5		ns
$t_{d(off)}$			40		ns
t_f			5		ns
R_{thJC}				1.15	K/W



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Source-Drain Diode

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
(T _{VJ} = 25°C, unless otherwise specified)				
I _S	V _{GS} = 0 V		5.2	A
V _{SD}	I _F = 5.2 A; V _{GS} = 0 V	0.9	1.2	V
t _{rr}	I _F = 5.2 A; -di _F /dt = 100 A/μs; V _R = 400 V		260	ns
Q _{RM}			3.1	μC
I _{RM}			24	A

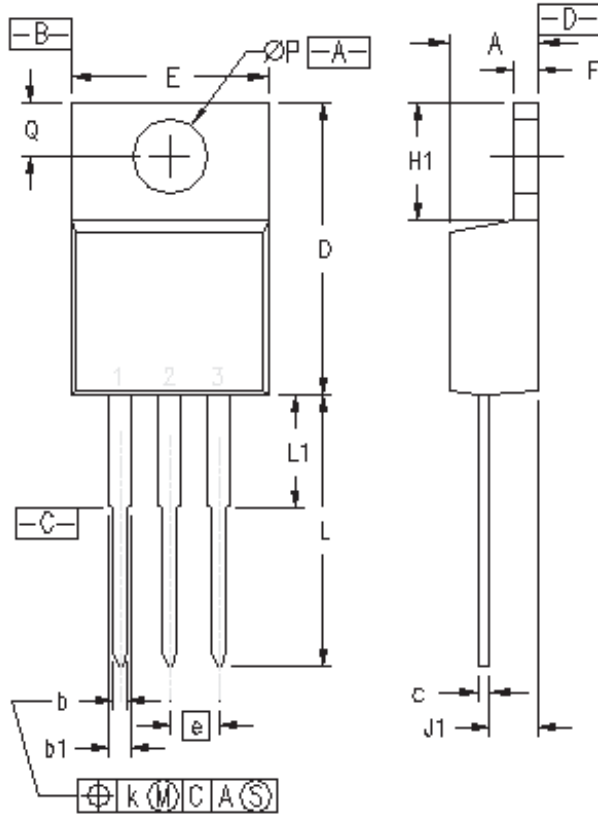
Component

Symbol	Conditions	Maximum Ratings	
T _{VJ}	operating	-55...+150	°C
T _{stg}		-55...+150	°C
M _d	mounting torque	0.4 ... 0.6	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R _{thCH}	with heatsink compound		0.50	K/W
Weight			2	g

IXYS **IXKP 10N60C5**

TO-220 AB Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-220 AB.

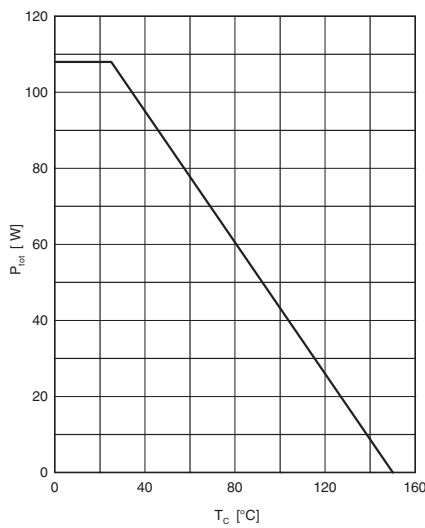


Fig. 1 Power dissipation

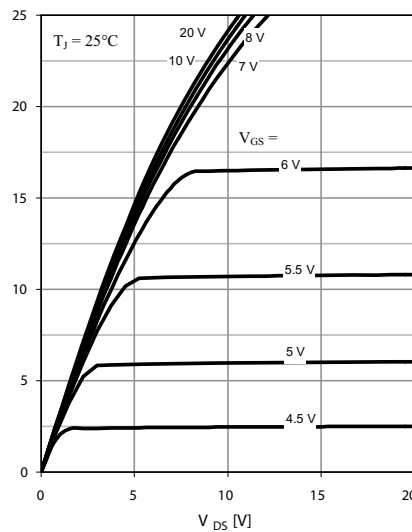


Fig. 2 Typ. output characteristics

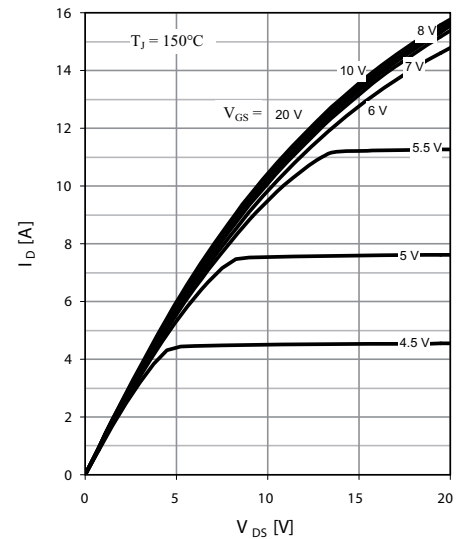


Fig. 3 Typ. output characteristics

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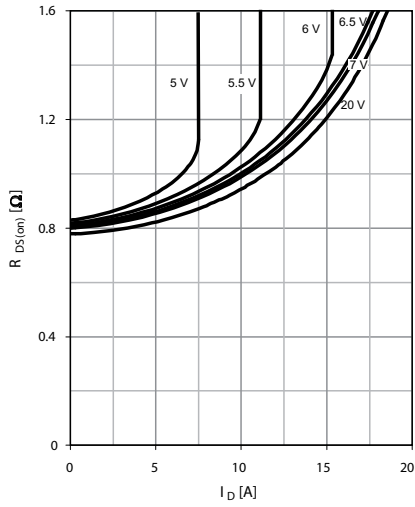


Fig. 4 Typ. drain-source on-state resistance characteristics of IGBT

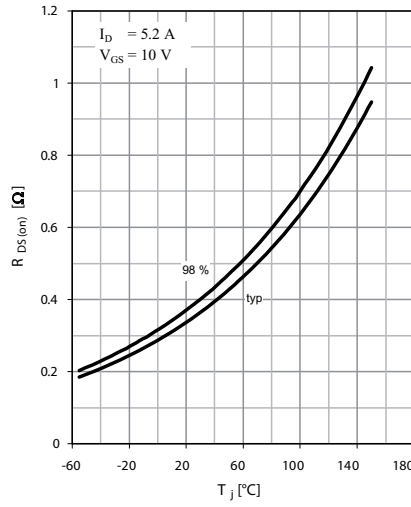


Fig. 5 Drain-source on-state resistance

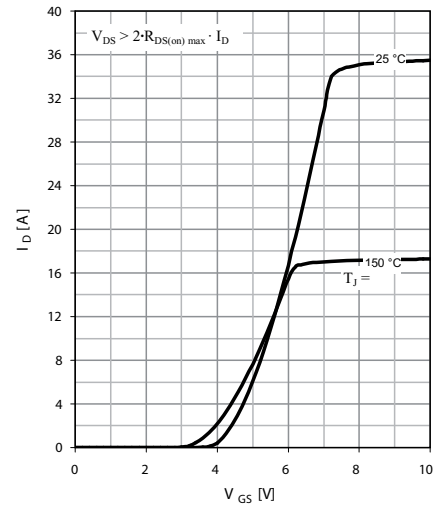


Fig. 6 Typ. transfer characteristics

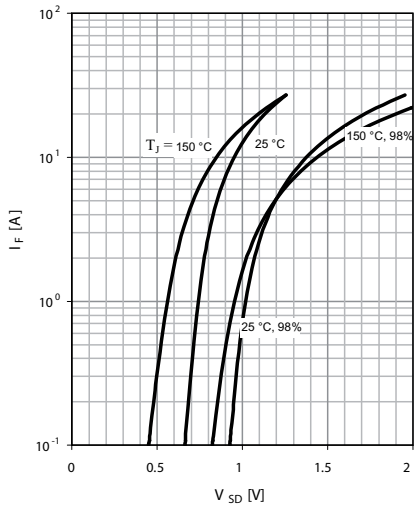


Fig. 7 Forward characteristic of reverse diode

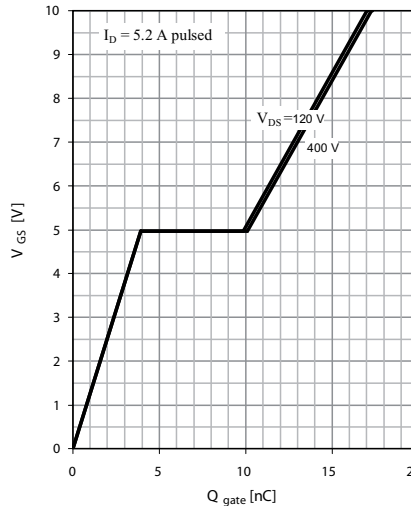


Fig. 8 Typ. gate charge

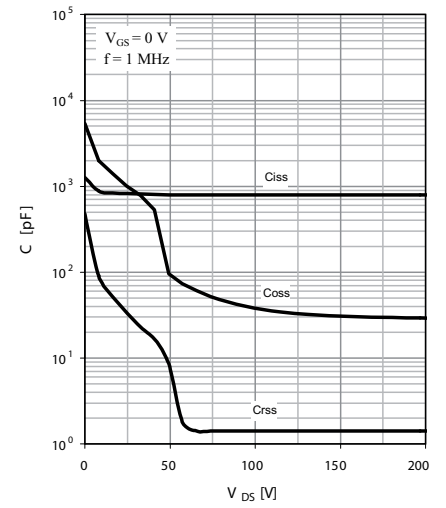


Fig. 9 Typ. capacitances

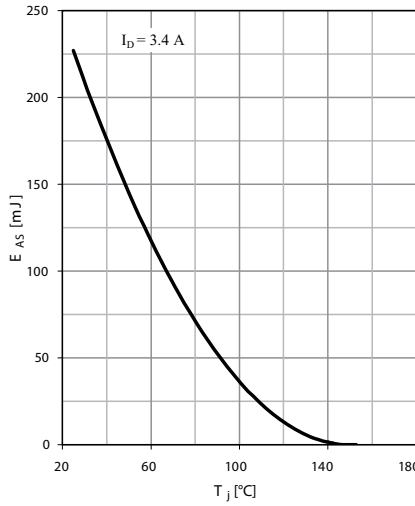


Fig. 10 Avalanche energy

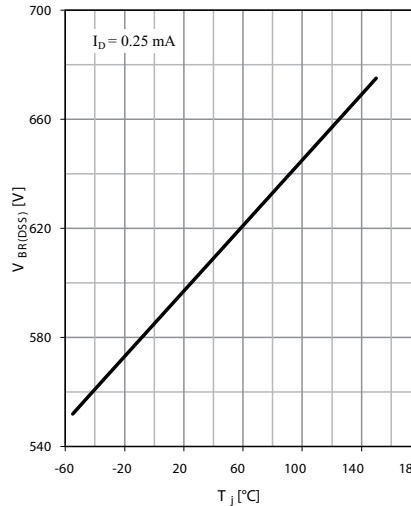


Fig. 11 Drain-source breakdown voltage

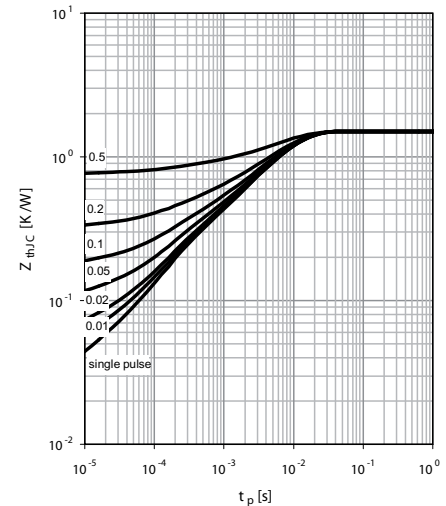


Fig. 12 Max. transient thermal impedance